TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L^2 - π -MOSIV)

2SJ315

DC-DC Converter

Unit: mm

FEATURES

• 4- Volt gate drive

• Low drain–source ON resistance : RDS (ON) = 0.25 Ω (typ.)

• High forward transfer admittance $: |Y_{fs}| = 3.0 \text{ S (typ.)}$

• Low leakage current : $IDSS = -100 \mu A (max) (VDS = -60 V)$

• Enhancement-mode : $V_{th} = -0.8 \sim -2.0 \text{ V (V}_{DS} = -10 \text{ V, I}_{D} = -1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-60	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	-60	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	-5	Α	
	Pulse(Note 1)	I _{DP}	-20	A	
Drain power dissipation (Tc = 25°C)		P_{D}	20	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

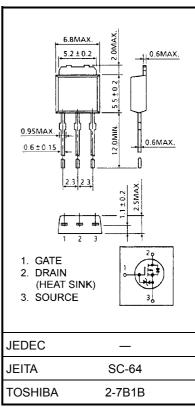
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	6.25	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	125	°C/W

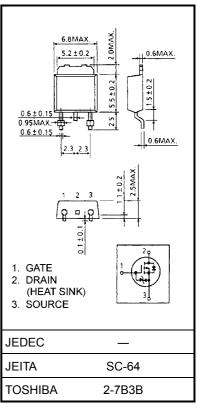
Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.

Please handle with caution.



Weight: 0.36 g (typ.)



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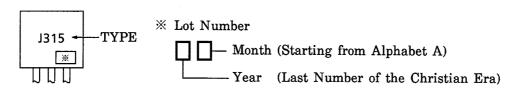
Electrical Characteristics (Ta = 25°C)

Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-off cu	rent	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	_	_	-100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-60	_	_	V
Gate threshold v	roltage	V _{th}	V _{DS} = -10 V, I _D = -1 mA	-0.8	_	-2.0	V
Drain-source ON resistance		R _{DS (ON)}	$V_{GS} = -4 \text{ V}, I_D = -2.5 \text{ A}$	_	0.31	0.40	Ω
			$V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	_	0.21	0.25	
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	1.8	3.0	_	S
Input capacitano	е	C _{iss}			500	_	
Reverse transfer	capacitance	C _{rss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	90	_	pF
Output capacitance		Coss		_	290	_	
Switching time	Rise time	t _r	$V_{GS} \stackrel{OV}{=} \stackrel{I_{D} = -2.5A}{\stackrel{OV}{=}} \stackrel{V_{OUT}}{\stackrel{V_{DD} = -30V}{=}} $	_	20	_	. ns
	Turn-on time	t _{on}		_	30	_	
	Fall time	t _f		_	30	_	
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{W}} = 10 \mu \text{s}$	_	140	_	
Total gate charge (Gate-source plus gate-drain)		Q_{g}	V _{DD} ≈ -48 V,	_	20	_	
Gate-source charge		Q_{gs}	$V_{GS} = -10 \text{ V},$ $I_{D} = -5 \text{ A}$		13	_	nC
Gate-drain ("miller") charge		Q_{gd}		_	7	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	1	-	-5	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	-	_	-20	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = -5 A, V _{GS} = 0 V	_	_	1.5	V

Marking



2 2002-06-27

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